

Diode Equation

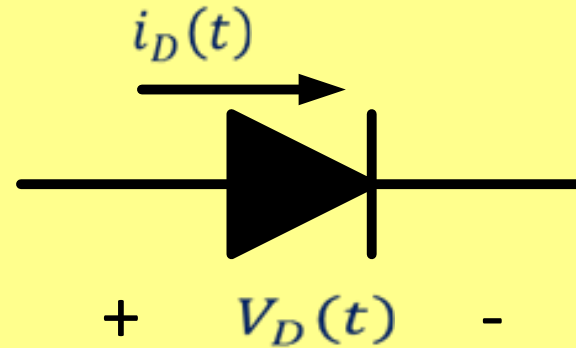
$$i_D(t) = I_S \left(e^{\frac{V_D(t)}{\eta V_T}} - 1 \right)$$

I_S : Reverse saturation current

$$I_S = 10^{-12}, 10^{-14} \text{ A}$$

η : eta

$$\eta = \begin{cases} 1 & \text{for Ge} \\ 2 & \text{for Si (small current)} \\ 1 & \text{for Si (large current)} \end{cases}$$



V_T = Thermal Voltage

$$V_T = \frac{T}{11600} \quad ; T \text{ in kelvin}$$

At Room Temp. $T=300\text{k}$

$\therefore V_T = 25.69 \text{ mv at Room Temp.}$

$$i_D(t) = I_S \left(e^{\frac{V_D(t)}{\eta V_T}} - 1 \right)$$

► The equation is a non linear equation

\therefore The Diode is non linear Device

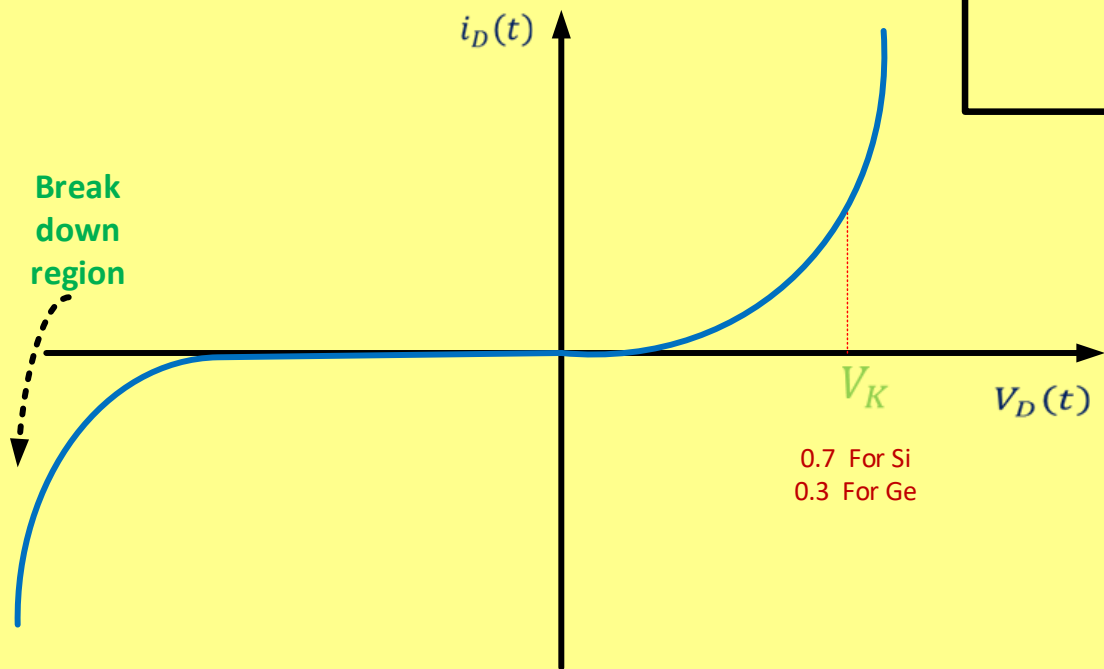
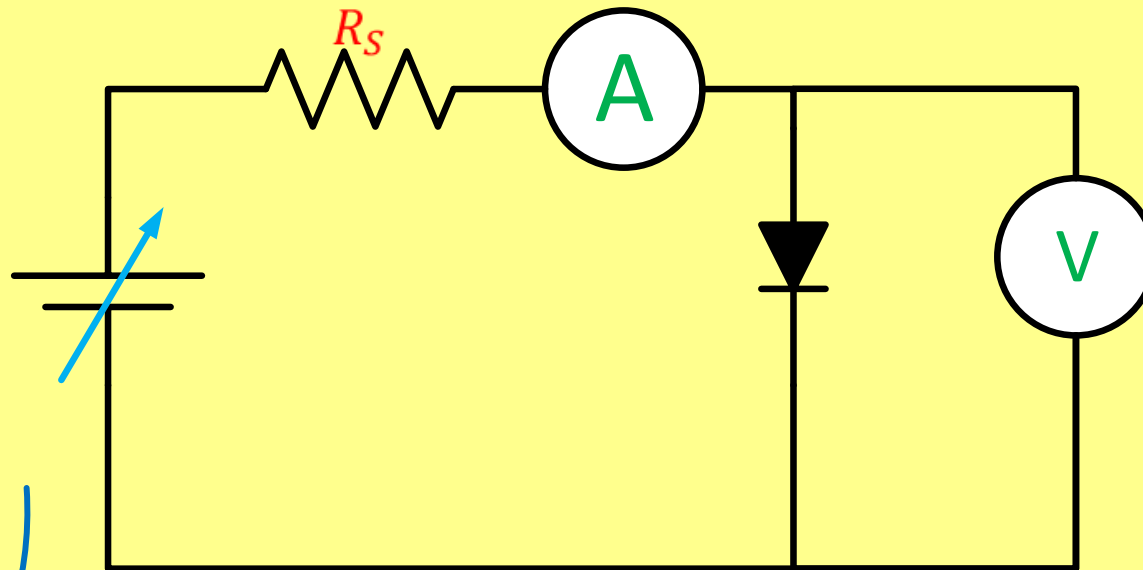
► For positive $V_D(t)$

$$i_D(t) = I_S \left(e^{\frac{V_D(t)}{\eta V_T}} \right)$$

► For negative $V_D(t)$

$$i_D(t) = -I_S$$

Diode V-I Characteristic curve



Approaches to Diode Circuit Analysis

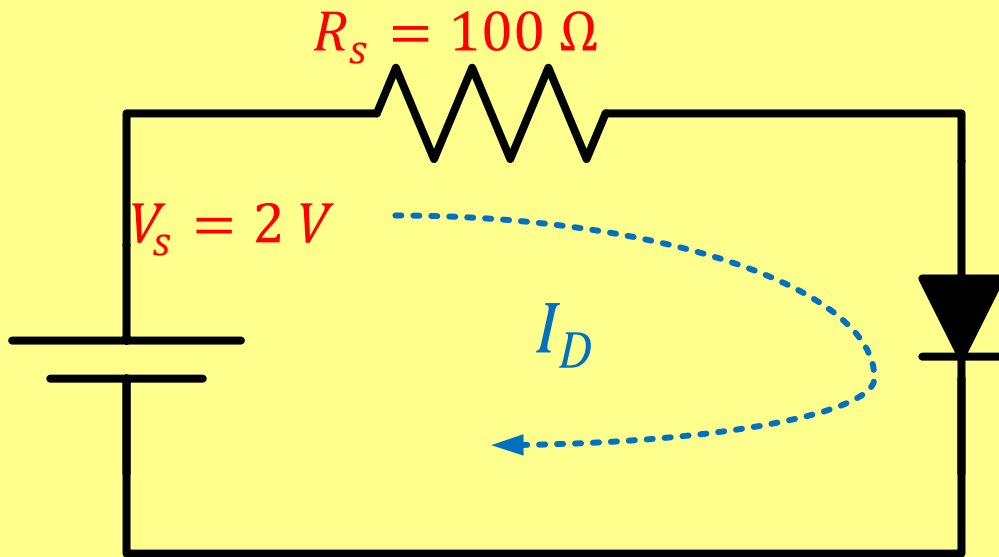
The rectifier diode is a **non linear** device .

There are essentially **three** basic approaches to the solution of such problem :

- 1- The use of non linear mathematics
- 2- The use of graphical techniques
- 3- The use of equivalent circuit (**models**)
 - **Piece wise linear models**

1) The use of non linear mathematic

- For the circuit shown, find I_D and V_D



Silicon:

$$\eta = 1.1$$

$$I_S = 10^{-14} \text{ A}$$

- KVL : $V_S = R_S I_D + V_D$

$$I_D = I_S \left(e^{\frac{V_D}{\eta V_T}} - 1 \right)$$

- Since the diode is **forward biased**, we could approximate

$$I_D = I_S \left(e^{\frac{V_D}{\eta V_T}} \right)$$

- Solving for $V_D = \eta V_T \ln \frac{I_D}{I_S}$

∴ We have two equations and two unknowns

$$V_S = R_S I_D + V_D \dots\dots\dots 1$$

$$V_D = \eta V_T \ln \frac{I_D}{I_S} \dots\dots\dots 2$$

$$\therefore V_S = R_S I_D + \eta V_T \ln \frac{I_D}{I_S}$$

- non linear equation

Iterative Analysis

1) Let $V_D = 0.7V$

$$I_D = \frac{2-0.7}{0.1k} = 13 \text{ mA}$$

$V_D = 0.7882392V$ The error is large

2) Let $V_D = 0.7882392V$

$$I_D = 12.117608 \text{ mA}$$

$V_D = 0.7862529V$ The error is small

$$I_D = \frac{V_S - V_D}{R_S}$$
$$V_D = \eta V_T \ln \frac{I_D}{I_S}$$

3) Let $V_D = 0.7862529\text{V}$

$$I_D = 12.137471 \text{ mA}$$

$$V_D = 0.7862991\text{V} \quad \text{The error getting smaller}$$

4) Let $V_D = 0.7862991\text{V}$

$$I_D = 12.137009\text{mA}$$

$$V_D = 0.786298066\text{V}$$

$$I_D = 12.137 \text{ mA}$$

$$V_D = 0.7863\text{V}$$

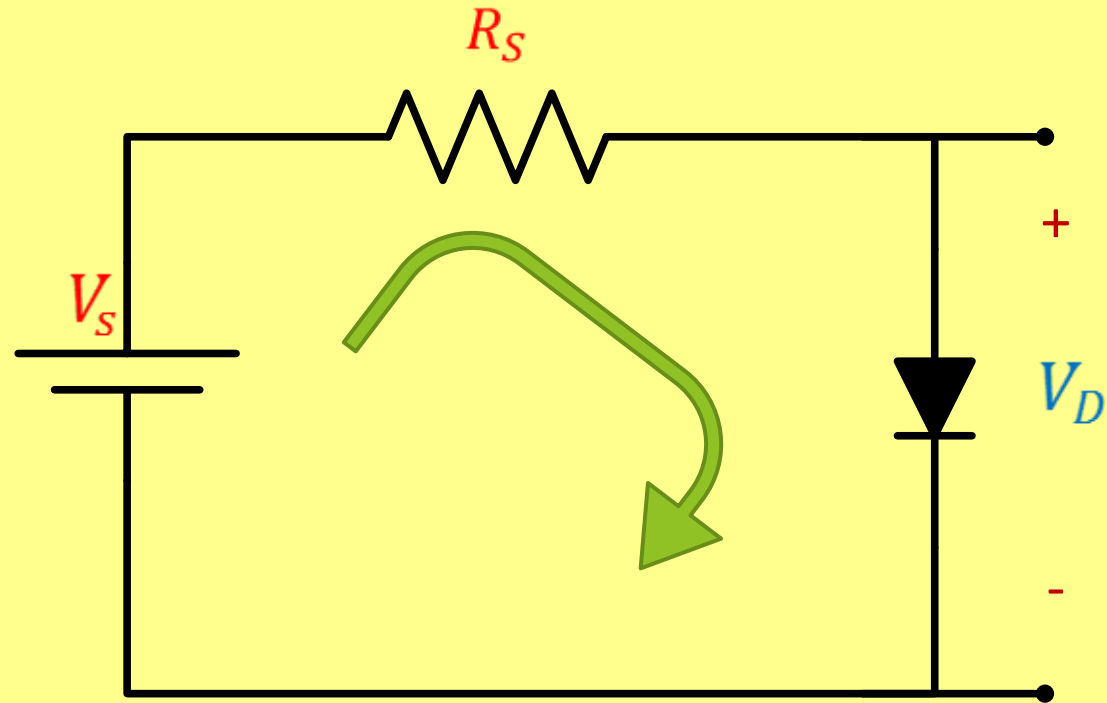
2) The use of graphical techniques

$$V_S = R_S I_D + V_D \quad \text{.....1}$$

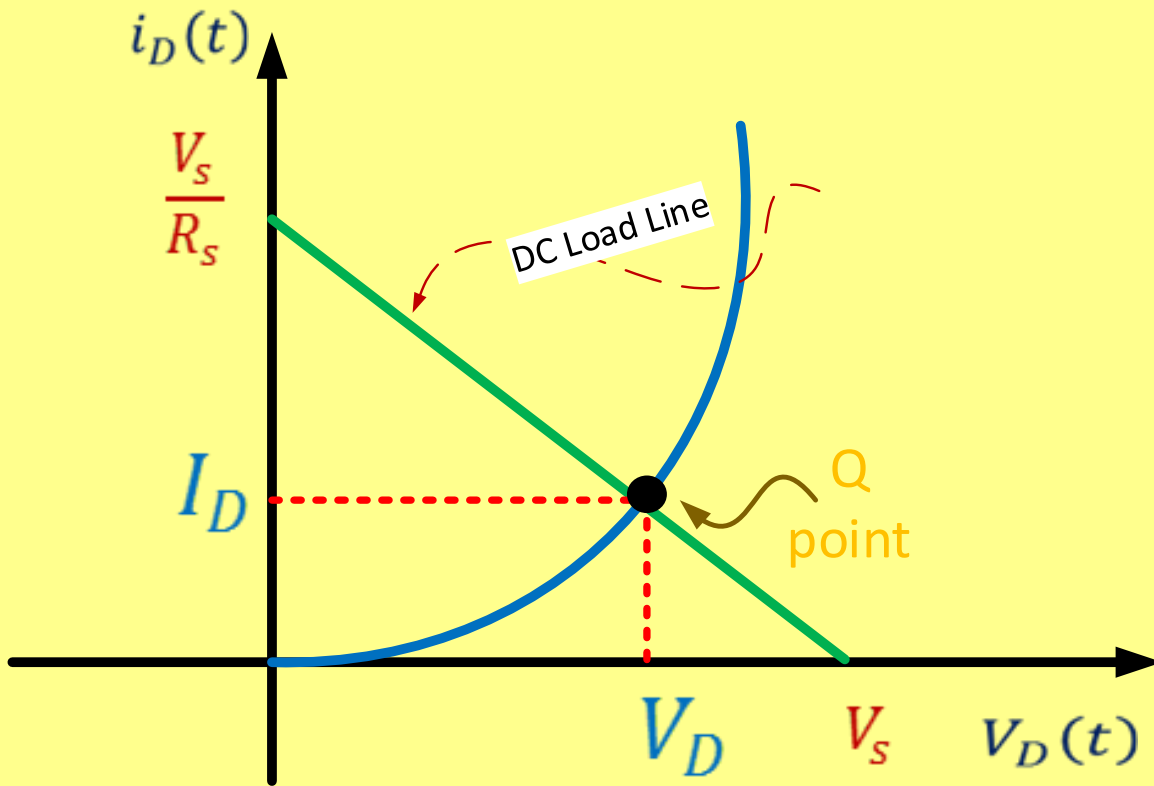
$$I_D = I_S \left(e^{\frac{V_D}{\eta V_T}} - 1 \right) \quad \text{.....2}$$

► Using equation 1

$$I_D = - \frac{1}{R_S} V_D + \frac{V_S}{R_S}$$



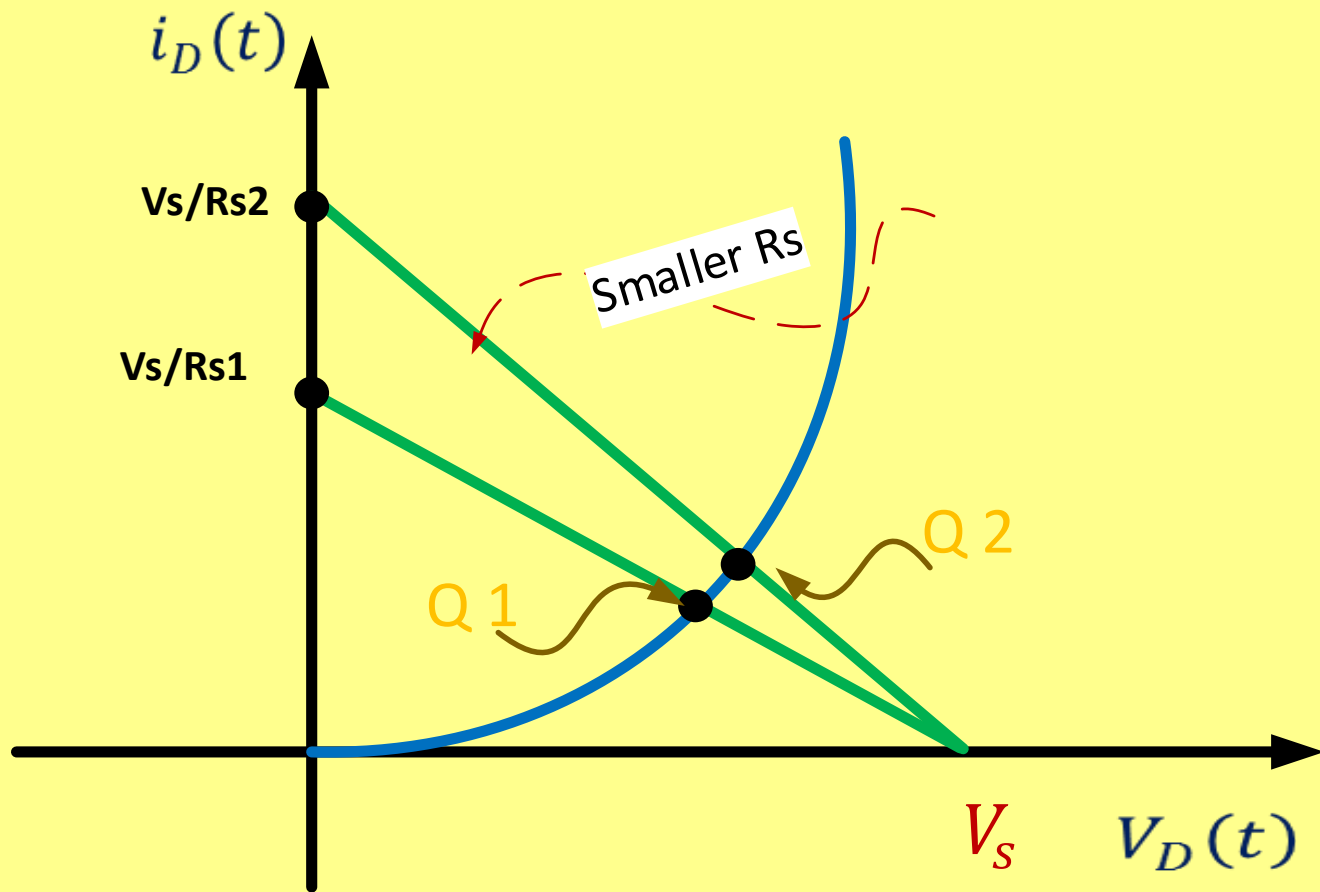
Drawing the two equations



$$I_D = - \frac{1}{R_S} V_D + \frac{V_S}{R_S}$$

- ▶ Q point = (I_{DQ}, V_{DQ}) = Quiescent point

The effect of R_s on the Qpoint



The effect of V_s on Qpoint

